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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Obsolete
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	55296
Number of I/O	151
Number of Gates	400000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	208-BFQFP
Supplier Device Package	208-PQFP (28x28)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/a3p400-2pq208i

ProASIC3 Device Family Overview

ProASIC3 DC and Switching Characteristics

Pin Descriptions

Package Pin Assignments

Datasheet Information

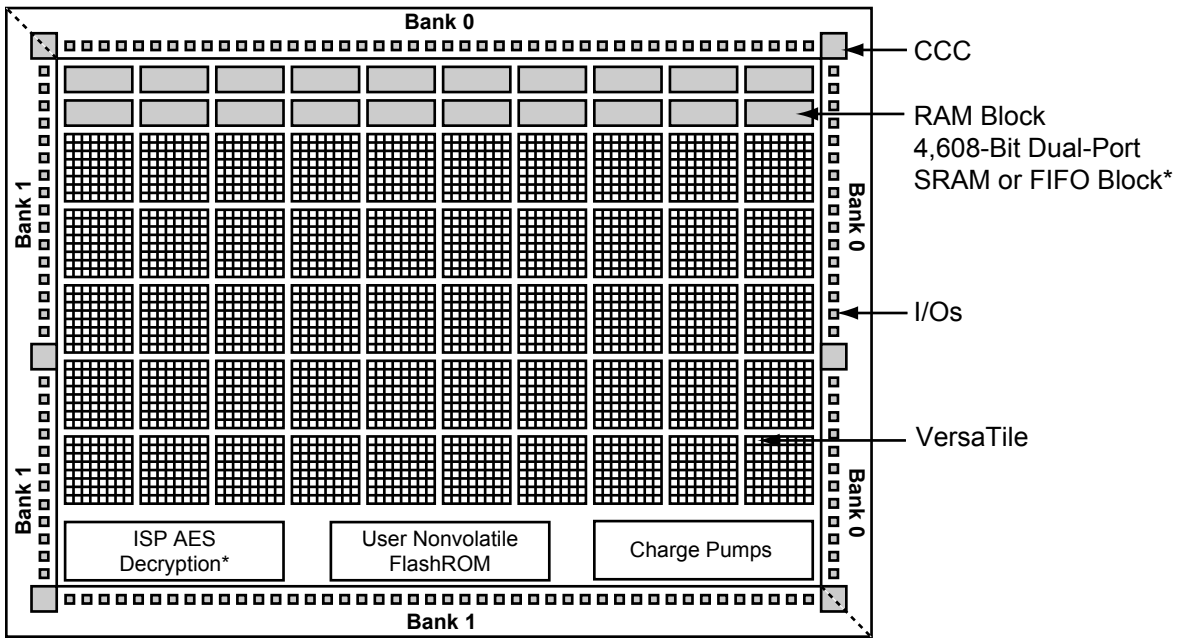
Advanced Flash Technology

The ProASIC3 family offers many benefits, including nonvolatility and reprogrammability through an advanced flash-based, 130-nm LVCMOS process with seven layers of metal. Standard CMOS design techniques are used to implement logic and control functions. The combination of fine granularity, enhanced flexible routing resources, and abundant flash switches allows for very high logic utilization without compromising device routability or performance. Logic functions within the device are interconnected through a four-level routing hierarchy.

Advanced Architecture

The proprietary ProASIC3 architecture provides granularity comparable to standard-cell ASICs. The ProASIC3 device consists of five distinct and programmable architectural features (Figure 1-1 and Figure 1-2 on page 1-4):

- FPGA VersaTiles
- Dedicated FlashROM
- Dedicated SRAM/FIFO memory†
- Extensive CCCs and PLLs†
- Advanced I/O structure



*Note: *Not supported by A3P015 and A3P030 devices*

Figure 1-1 • **ProASIC3 Device Architecture Overview with Two I/O Banks (A3P015, A3P030, A3P060, and A3P125)**

† *The A3P015 and A3P030 do not support PLL or SRAM.*

Table 2-26 • Summary of I/O Timing Characteristics—Software Default Settings –2 Speed Grade, Commercial-Case Conditions: T_J = 70°C, Worst Case VCC = 1.425 V, Worst-Case VCCI (per standard) Standard I/O Banks

I/O Standard	Drive Strength	Equiv. Software Default Drive Strength Option[1]	Slew Rate	Capacitive Load (pF)	External Resistor	t_{DOUT} (ns)	t_{DP} (ns)	t_{DIN} (ns)	t_{PY} (ns)	t_{EOUT} (ns)	t_{ZL} (ns)	t_{ZH} (ns)	t_{LZ} (ns)	t_{HZ} (ns)	Units
3.3 V LVTTL / 3.3 V LVCMOS	8 mA	8 mA	High	35	–	0.45	3.29	0.03	0.75	0.32	3.36	2.80	1.79	2.01	ns
3.3 V LVCMOS Wide Range[2]	100 µA	8 mA	High	35	–	0.45	5.09	0.03	1.13	0.32	5.09	4.25	2.77	3.11	ns
2.5 V LVCMOS	8 mA	8 mA	High	35	–	0.45	3.56	0.03	0.96	0.32	3.40	3.56	1.78	1.91	ns
1.8 V LVCMOS	4 mA	4 mA	High	35	–	0.45	4.74	0.03	0.90	0.32	4.02	4.74	1.80	1.85	ns
1.5 V LVCMOS	2 mA	2 mA	High	35	–	0.45	5.71	0.03	1.06	0.32	4.71	5.71	1.83	1.83	ns

Notes:

1. *The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is ±100 µA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.*
2. *All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD-8B specification.*
3. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*

Table 2-53 • 3.3 V LVTTL / 3.3 V LVCMOS Low Slew
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V
Applicable to Standard Plus I/O Banks

Drive Strength	Equiv. Software Default Drive Strength Option[1]	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
100 µA	2 mA	Std.	0.60	14.97	0.04	1.52	0.43	14.97	12.79	3.52	3.41	18.36	16.18	ns
		–1	0.51	12.73	0.04	1.29	0.36	12.73	10.88	2.99	2.90	15.62	13.77	ns
		–2	0.45	11.18	0.03	1.14	0.32	11.18	9.55	2.63	2.55	13.71	12.08	ns
100 µA	4 mA	Std.	0.60	10.36	0.04	1.52	0.43	10.36	8.93	3.99	4.24	13.75	12.33	ns
		–1	0.51	8.81	0.04	1.29	0.36	8.81	7.60	3.39	3.60	11.70	10.49	ns
		–2	0.45	7.74	0.03	1.14	0.32	7.74	6.67	2.98	3.16	10.27	9.21	ns
100 µA	6 mA	Std.	0.60	10.36	0.04	1.52	0.43	10.36	8.93	3.99	4.24	13.75	12.33	ns
		–1	0.51	8.81	0.04	1.29	0.36	8.81	7.60	3.39	3.60	11.70	10.49	ns
		–2	0.45	7.74	0.03	1.14	0.32	7.74	6.67	2.98	3.16	10.27	9.21	ns
100 µA	8 mA	Std.	0.60	7.81	0.04	1.52	0.43	7.81	6.85	4.32	4.76	11.20	10.24	ns
		–1	0.51	6.64	0.04	1.29	0.36	6.64	5.82	3.67	4.05	9.53	8.71	ns
		–2	0.45	5.83	0.03	1.14	0.32	5.83	5.11	3.22	3.56	8.36	7.65	ns
100 µA	16 mA	Std.	0.60	7.81	0.04	1.52	0.43	7.81	6.85	4.32	4.76	11.20	10.24	ns
		–1	0.51	6.64	0.04	1.29	0.36	6.64	5.82	3.67	4.05	9.53	8.71	ns
		–2	0.45	5.83	0.03	1.14	0.32	5.83	5.11	3.22	3.56	8.36	7.65	ns

Notes:

1. *The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is ±100 µA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*

Table 2-55 • 3.3 V LVTTL / 3.3 V LVCMOS Low Slew
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V
Applicable to Standard I/O Banks

Drive Strength	Equiv. Software Default Drive Strength Option[1]	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
100 µA	2 mA	Std.	0.60	14.64	0.04	1.52	0.43	14.64	12.97	3.21	3.15	ns
		–1	0.51	12.45	0.04	1.29	0.36	12.45	11.04	2.73	2.68	ns
		–2	0.45	10.93	0.03	1.13	0.32	10.93	9.69	2.39	2.35	ns
100 µA	4 mA	Std.	0.60	14.64	0.04	1.52	0.43	14.64	12.97	3.21	3.15	ns
		–1	0.51	12.45	0.04	1.29	0.36	12.45	11.04	2.73	2.68	ns
		–2	0.45	10.93	0.03	1.13	0.32	10.93	9.69	2.39	2.35	ns
100 µA	6 mA	Std.	0.60	10.16	0.04	1.52	0.43	10.16	9.08	3.71	3.98	ns
		–1	0.51	8.64	0.04	1.29	0.36	8.64	7.73	3.15	3.39	ns
		–2	0.45	7.58	0.03	1.13	0.32	7.58	6.78	2.77	2.97	ns
100 µA	8 mA	Std.	0.60	10.16	0.04	1.52	0.43	10.16	9.08	3.71	3.98	ns
		–1	0.51	8.64	0.04	1.29	0.36	8.64	7.73	3.15	3.39	ns
		–2	0.45	7.58	0.03	1.13	0.32	7.58	6.78	2.77	2.97	ns

Notes:

1. *The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is ±100 µA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*

3.3 V PCI, 3.3 V PCI-X

Peripheral Component Interface for 3.3 V standard specifies support for 33 MHz and 66 MHz PCI Bus applications.

Table 2-86 • Minimum and Maximum DC Input and Output Levels

3.3 V PCI/PCI-X	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL	IIH
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max,. V	Min. V	mA	mA	Max. mA[1]	Max. mA[1]	µA[2]	µA[2]
Per PCI specification	Per PCI curves										10	10

Notes:

1. *Currents are measured at high temperature (100°C junction temperature) and maximum voltage.*
2. *Currents are measured at 85°C junction temperature.*

AC loadings are defined per the PCI/PCI-X specifications for the datapath; Microsemi loadings for enable path characterization are described in Figure 2-11.

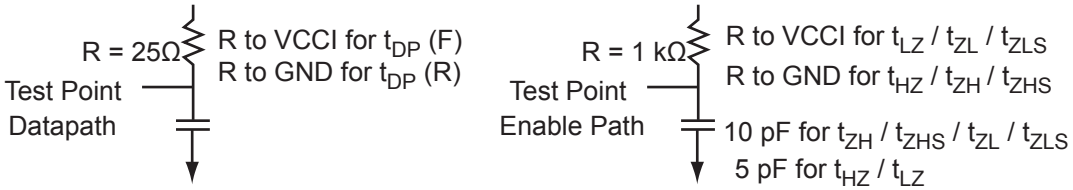


Figure 2-11 • AC Loading

AC loadings are defined per PCI/PCI-X specifications for the datapath; Microsemi loading for tristate is described in Table 2-87.

Table 2-87 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	C_{LOAD} (pF)
0	3.3	0.285 * VCCI for $t_{DP(R)}$ 0.615 * VCCI for $t_{DP(F)}$	10

*Note: *Measuring point = V_{trip}. See Table 2-22 on page 2-22 for a complete table of trip points.*

I/O Register Specifications

Fully Registered I/O Buffers with Synchronous Enable and Asynchronous Preset

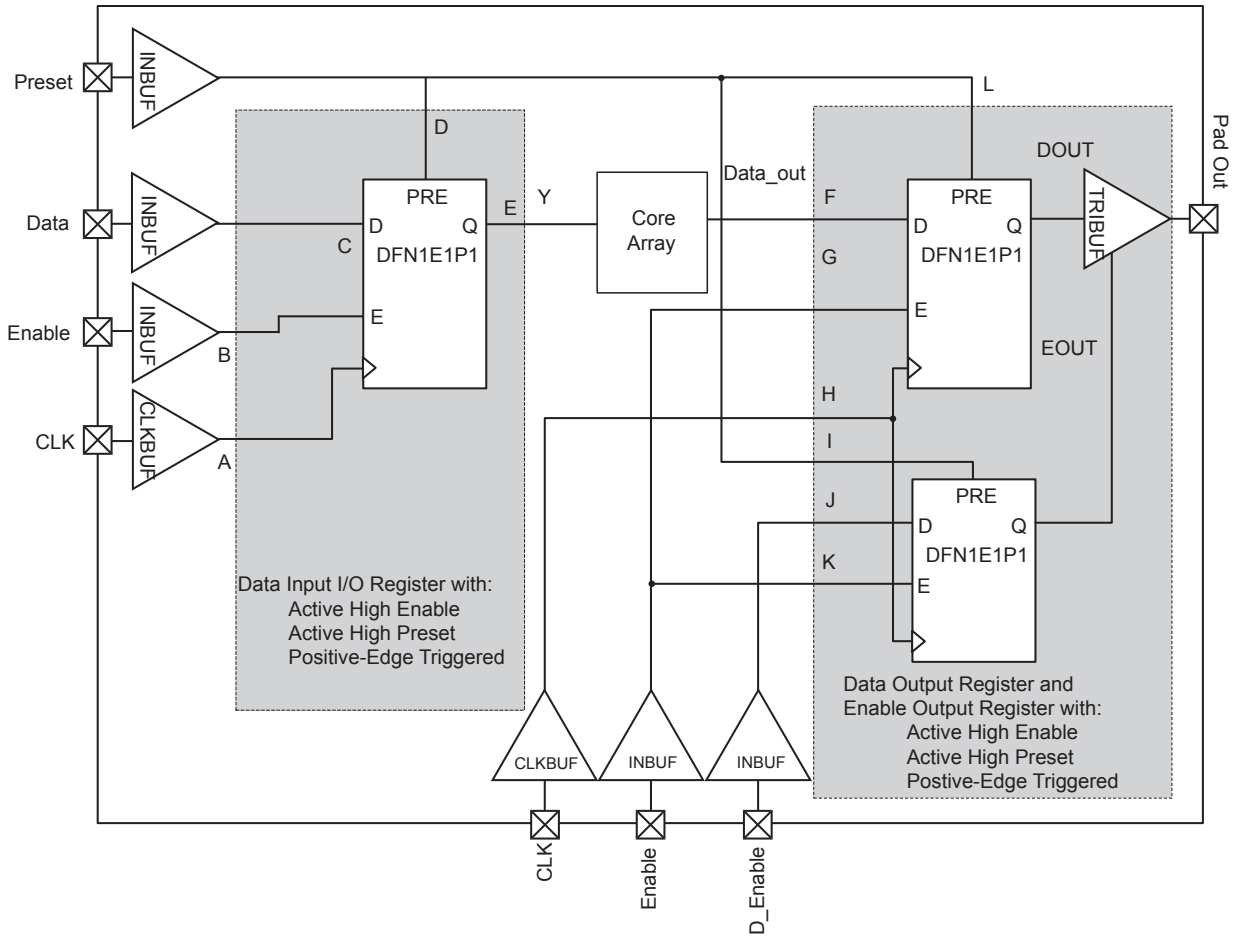


Figure 2-15 • **Timing Model of Registered I/O Buffers with Synchronous Enable and Asynchronous Preset**

Output DDR Module

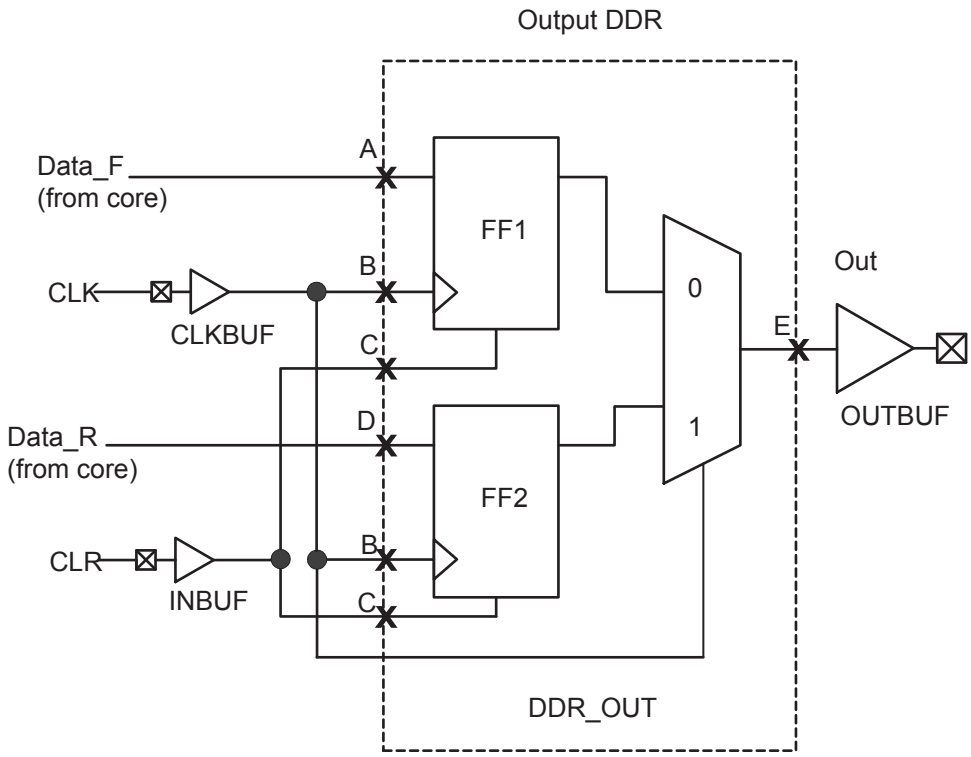


Figure 2-22 • **Output DDR Timing Model**

Table 2-103 • **Parameter Definitions**

Parameter Name	Parameter Definition	Measuring Nodes (from, to)
$t_{DDROCLKQ}$	Clock-to-Out	B, E
$t_{DDROCLR2Q}$	Asynchronous Clear-to-Out	C, E
$t_{DDROREMCLR}$	Clear Removal	C, B
$t_{DDRORECCLR}$	Clear Recovery	C, B
$t_{DDROSUD1}$	Data Setup Data_F	A, B
$t_{DDROSUD2}$	Data Setup Data_R	D, B
$t_{DDROHD1}$	Data Hold Data_F	A, B
$t_{DDROHD2}$	Data Hold Data_R	D, B

Timing Waveforms

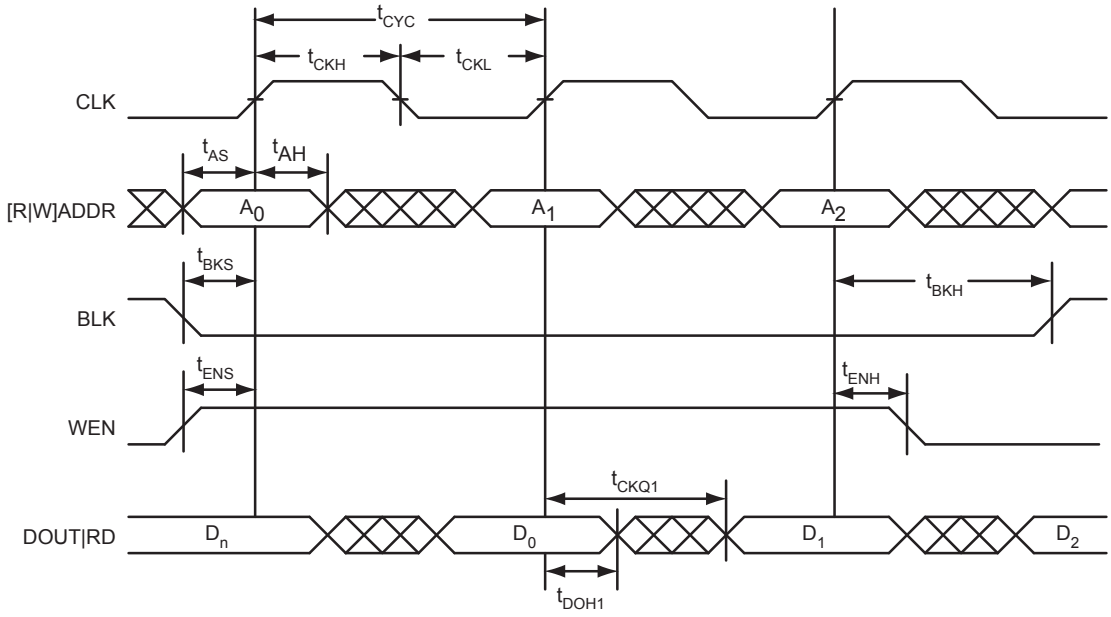


Figure 2-31 • **RAM Read for Pass-Through Output. Applicable to Both RAM4K9 and RAM512x18.**

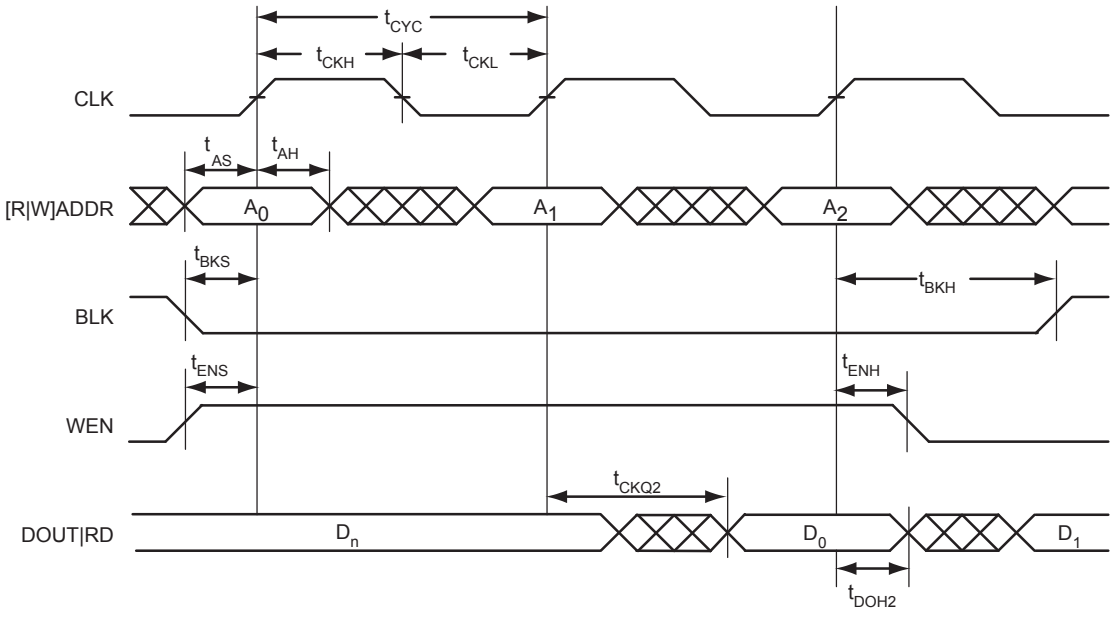


Figure 2-32 • **RAM Read for Pipelined Output. Applicable to Both RAM4K9 and RAM512x18.**

Timing Characteristics

Table 2-116 • RAM4K9
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V

Parameter	Description	–2	–1	Std.	Units
t_{AS}	Address setup time	0.25	0.28	0.33	ns
t_{AH}	Address hold time	0.00	0.00	0.00	ns
t_{ENS}	REN, WEN setup time	0.14	0.16	0.19	ns
t_{ENH}	REN, WEN hold time	0.10	0.11	0.13	ns
t_{BKS}	BLK setup time	0.23	0.27	0.31	ns
t_{BKH}	BLK hold time	0.02	0.02	0.02	ns
t_{DS}	Input data (DIN) setup time	0.18	0.21	0.25	ns
t_{DH}	Input data (DIN) hold time	0.00	0.00	0.00	ns
t_{CKQ1}	Clock High to new data valid on DOUT (output retained, WMODE = 0)	2.36	2.68	3.15	ns
	Clock High to new data valid on DOUT (flow-through, WMODE = 1)	1.79	2.03	2.39	ns
t_{CKQ2}	Clock High to new data valid on DOUT (pipelined)	0.89	1.02	1.20	ns
t_{C2CWWL} [1]	Address collision clk-to-clk delay for reliable write after write on same address—Applicable to Closing Edge	0.33	0.28	0.25	ns
t_{C2CWWH} [1]	Address collision clk-to-clk delay for reliable write after write on same address—Applicable to Rising Edge	0.30	0.26	0.23	ns
t_{C2CRWH} [1]	Address collision clk-to-clk delay for reliable read access after write on same address—Applicable to Opening Edge	0.45	0.38	0.34	ns
t_{C2CWRH} [1]	Address collision clk-to-clk delay for reliable write access after read on same address— Applicable to Opening Edge	0.49	0.42	0.37	ns
t_{RSTBQ}	RESET Low to data out Low on DOUT (flow-through)	0.92	1.05	1.23	ns
	RESET Low to Data Out Low on DOUT (pipelined)	0.92	1.05	1.23	ns
$t_{REMRSTB}$	RESET removal	0.29	0.33	0.38	ns
$t_{RECRSTB}$	RESET recovery	1.50	1.71	2.01	ns
$t_{MPWRSTB}$	RESET minimum pulse width	0.21	0.24	0.29	ns
t_{CYC}	Clock cycle time	3.23	3.68	4.32	ns
F_{MAX}	Maximum frequency	310	272	231	MHz

Notes:

1. *For more information, refer to the application note Simultaneous Read-Write Operations in Dual-Port SRAM for Flash-Based cSoCs and FPGAs.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*

Table 2-117 • RAM512X18
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V

Parameter	Description	–2	–1	Std.	Units
t_{AS}	Address setup time	0.25	0.28	0.33	ns
t_{AH}	Address hold time	0.00	0.00	0.00	ns
t_{ENS}	REN, WEN setup time	0.13	0.15	0.17	ns
t_{ENH}	REN, WEN hold time	0.10	0.11	0.13	ns
t_{DS}	Input data (WD) setup time	0.18	0.21	0.25	ns
t_{DH}	Input data (WD) hold time	0.00	0.00	0.00	ns
t_{CKQ1}	Clock High to new data valid on RD (output retained)	2.16	2.46	2.89	ns
t_{CKQ2}	Clock High to new data valid on RD (pipelined)	0.90	1.02	1.20	ns
t_{C2CRWH}[1]	Address collision clk-to-clk delay for reliable read access after write on same address—Applicable to Opening Edge	0.50	0.43	0.38	ns
t_{C2CWRH}[1]	Address collision clk-to-clk delay for reliable write access after read on same address—Applicable to Opening Edge	0.59	0.50	0.44	ns
t_{RSTBQ}	RESET Low to data out Low on RD (flow-through)	0.92	1.05	1.23	ns
	RESET Low to data out Low on RD (pipelined)	0.92	1.05	1.23	ns
$t_{REMRSTB}$	RESET removal	0.29	0.33	0.38	ns
$t_{RECRSTB}$	RESET recovery	1.50	1.71	2.01	ns
$t_{MPWRSTB}$	RESET minimum pulse width	0.21	0.24	0.29	ns
t_{CYC}	Clock cycle time	3.23	3.68	4.32	ns
F_{MAX}	Maximum frequency	310	272	231	MHz

Notes:

1. *For more information, refer to the application note Simultaneous Read-Write Operations in Dual-Port SRAM for Flash-Based cSoCs and FPGAs.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*

QN132	
Pin Number	A3P060 Function
A1	GAB2/IO00RSB1
A2	IO93RSB1
A3	VCCIB1
A4	GFC1/IO89RSB1
A5	GFB0/IO86RSB1
A6	VCCPLF
A7	GFA1/IO84RSB1
A8	GFC2/IO81RSB1
A9	IO78RSB1
A10	VCC
A11	GEB1/IO75RSB1
A12	GEA0/IO72RSB1
A13	GEC2/IO69RSB1
A14	IO65RSB1
A15	VCC
A16	IO64RSB1
A17	IO63RSB1
A18	IO62RSB1
A19	IO61RSB1
A20	IO58RSB1
A21	GDB2/IO55RSB1
A22	NC
A23	GDA2/IO54RSB1
A24	TDI
A25	TRST
A26	GDC1/IO48RSB0
A27	VCC
A28	IO47RSB0
A29	GCC2/IO46RSB0
A30	GCA2/IO44RSB0
A31	GCA0/IO43RSB0
A32	GCB1/IO40RSB0
A33	IO36RSB0
A34	VCC
A35	IO31RSB0
A36	GBA2/IO28RSB0

QN132	
Pin Number	A3P060 Function
A37	GBB1/IO25RSB0
A38	GBC0/IO22RSB0
A39	VCCIB0
A40	IO21RSB0
A41	IO18RSB0
A42	IO15RSB0
A43	IO14RSB0
A44	IO11RSB0
A45	GAB1/IO08RSB0
A46	NC
A47	GAB0/IO07RSB0
A48	IO04RSB0
B1	IO01RSB1
B2	GAC2/IO94RSB1
B3	GND
B4	GFC0/IO88RSB1
B5	VCOMPLF
B6	GND
B7	GFB2/IO82RSB1
B8	IO79RSB1
B9	GND
B10	GEB0/IO74RSB1
B11	VMV1
B12	GEB2/IO70RSB1
B13	IO67RSB1
B14	GND
B15	NC
B16	NC
B17	GND
B18	IO59RSB1
B19	GDC2/IO56RSB1
B20	GND
B21	GNDQ
B22	TMS
B23	TDO
B24	GDC0/IO49RSB0

QN132	
Pin Number	A3P060 Function
B25	GND
B26	NC
B27	GCB2/IO45RSB0
B28	GND
B29	GCB0/IO41RSB0
B30	GCC1/IO38RSB0
B31	GND
B32	GBB2/IO30RSB0
B33	VMV0
B34	GBA0/IO26RSB0
B35	GBC1/IO23RSB0
B36	GND
B37	IO20RSB0
B38	IO17RSB0
B39	GND
B40	IO12RSB0
B41	GAC0/IO09RSB0
B42	GND
B43	GAA1/IO06RSB0
B44	GNDQ
C1	GAA2/IO02RSB1
C2	IO95RSB1
C3	VCC
C4	GFB1/IO87RSB1
C5	GFA0/IO85RSB1
C6	GFA2/IO83RSB1
C7	IO80RSB1
C8	VCCIB1
C9	GEA1/IO73RSB1
C10	GNDQ
C11	GEA2/IO71RSB1
C12	IO68RSB1
C13	VCCIB1
C14	NC
C15	NC
C16	IO60RSB1

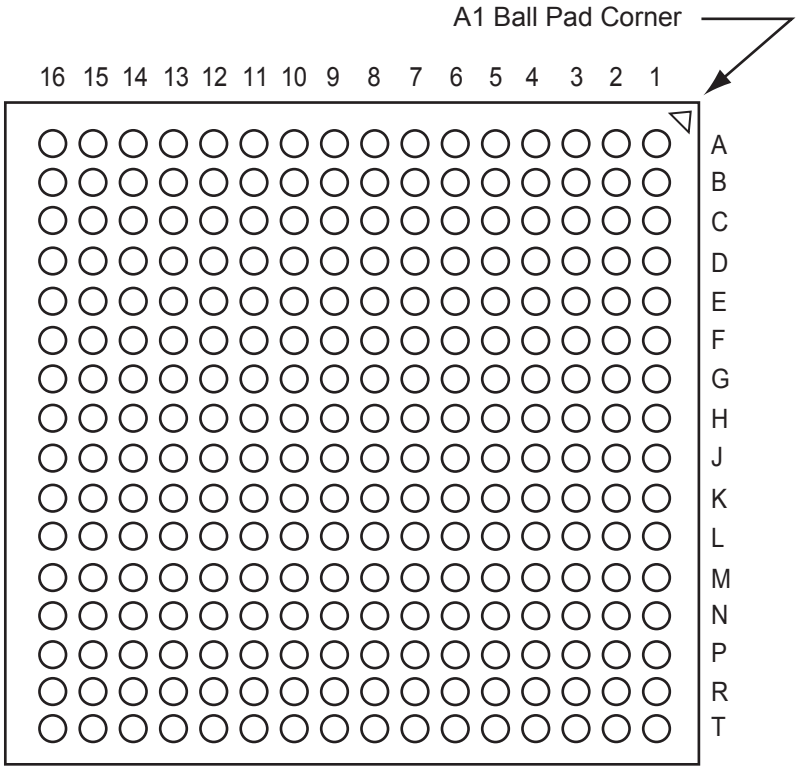
VQ100	
Pin Number	A3P060 Function
1	GND
2	GAA2/IO51RSB1
3	IO52RSB1
4	GAB2/IO53RSB1
5	IO95RSB1
6	GAC2/IO94RSB1
7	IO93RSB1
8	IO92RSB1
9	GND
10	GFB1/IO87RSB1
11	GFB0/IO86RSB1
12	VCOMPLF
13	GFA0/IO85RSB1
14	VCCPLF
15	GFA1/IO84RSB1
16	GFA2/IO83RSB1
17	VCC
18	VCCIB1
19	GEC1/IO77RSB1
20	GEB1/IO75RSB1
21	GEB0/IO74RSB1
22	GEA1/IO73RSB1
23	GEA0/IO72RSB1
24	VMV1
25	GNDQ
26	GEA2/IO71RSB1
27	GEB2/IO70RSB1
28	GEC2/IO69RSB1
29	IO68RSB1
30	IO67RSB1
31	IO66RSB1
32	IO65RSB1
33	IO64RSB1
34	IO63RSB1
35	IO62RSB1
36	IO61RSB1

VQ100	
Pin Number	A3P060 Function
37	VCC
38	GND
39	VCCIB1
40	IO60RSB1
41	IO59RSB1
42	IO58RSB1
43	IO57RSB1
44	GDC2/IO56RSB1
45	GDB2/IO55RSB1
46	GDA2/IO54RSB1
47	TCK
48	TDI
49	TMS
50	VMV1
51	GND
52	VPUMP
53	NC
54	TDO
55	TRST
56	VJTAG
57	GDA1/IO49RSB0
58	GDC0/IO46RSB0
59	GDC1/IO45RSB0
60	GCC2/IO43RSB0
61	GCB2/IO42RSB0
62	GCA0/IO40RSB0
63	GCA1/IO39RSB0
64	GCC0/IO36RSB0
65	GCC1/IO35RSB0
66	VCCIB0
67	GND
68	VCC
69	IO31RSB0
70	GBC2/IO29RSB0
71	GBB2/IO27RSB0
72	IO26RSB0

VQ100	
Pin Number	A3P060 Function
73	GBA2/IO25RSB0
74	VMV0
75	GNDQ
76	GBA1/IO24RSB0
77	GBA0/IO23RSB0
78	GBB1/IO22RSB0
79	GBB0/IO21RSB0
80	GBC1/IO20RSB0
81	GBC0/IO19RSB0
82	IO18RSB0
83	IO17RSB0
84	IO15RSB0
85	IO13RSB0
86	IO11RSB0
87	VCCIB0
88	GND
89	VCC
90	IO10RSB0
91	IO09RSB0
92	IO08RSB0
93	GAC1/IO07RSB0
94	GAC0/IO06RSB0
95	GAB1/IO05RSB0
96	GAB0/IO04RSB0
97	GAA1/IO03RSB0
98	GAA0/IO02RSB0
99	IO01RSB0
100	IO00RSB0

FG144	
Pin Number	**A3P060 Function**
K1	GEB0/IO74RSB1
K2	GEA1/IO73RSB1
K3	GEA0/IO72RSB1
K4	GEA2/IO71RSB1
K5	IO65RSB1
K6	IO64RSB1
K7	GND
K8	IO57RSB1
K9	GDC2/IO56RSB1
K10	GND
K11	GDA0/IO50RSB0
K12	GDB0/IO48RSB0
L1	GND
L2	VMV1
L3	GEB2/IO70RSB1
L4	IO67RSB1
L5	VCCIB1
L6	IO62RSB1
L7	IO59RSB1
L8	IO58RSB1
L9	TMS
L10	VJTAG
L11	VMV1
L12	TRST
M1	GNDQ
M2	GEC2/IO69RSB1
M3	IO68RSB1
M4	IO66RSB1
M5	IO63RSB1
M6	IO61RSB1
M7	IO60RSB1
M8	NC
M9	TDI
M10	VCCIB1
M11	VPUMP
M12	GNDQ

FG256 – Bottom View



Note

For more information on package drawings, see *PD3068: Package Mechanical Drawings*.

FG256	
Pin Number	A3P250 Function
A1	GND
A2	GAA0/IO00RSB0
A3	GAA1/IO01RSB0
A4	GAB0/IO02RSB0
A5	IO07RSB0
A6	IO10RSB0
A7	IO11RSB0
A8	IO15RSB0
A9	IO20RSB0
A10	IO25RSB0
A11	IO29RSB0
A12	IO33RSB0
A13	GBB1/IO38RSB0
A14	GBA0/IO39RSB0
A15	GBA1/IO40RSB0
A16	GND
B1	GAB2/IO117UDB3
B2	GAA2/IO118UDB3
B3	NC
B4	GAB1/IO03RSB0
B5	IO06RSB0
B6	IO09RSB0
B7	IO12RSB0
B8	IO16RSB0
B9	IO21RSB0
B10	IO26RSB0
B11	IO30RSB0
B12	GBC1/IO36RSB0
B13	GBB0/IO37RSB0
B14	NC
B15	GBA2/IO41PDB1
B16	IO41NDB1
C1	IO117VDB3
C2	IO118VDB3
C3	NC
C4	NC

FG256	
Pin Number	A3P250 Function
C5	GAC0/IO04RSB0
C6	GAC1/IO05RSB0
C7	IO13RSB0
C8	IO17RSB0
C9	IO22RSB0
C10	IO27RSB0
C11	IO31RSB0
C12	GBC0/IO35RSB0
C13	IO34RSB0
C14	NC
C15	IO42NPB1
C16	IO44PDB1
D1	IO114VDB3
D2	IO114UDB3
D3	GAC2/IO116UDB3
D4	NC
D5	GNDQ
D6	IO08RSB0
D7	IO14RSB0
D8	IO18RSB0
D9	IO23RSB0
D10	IO28RSB0
D11	IO32RSB0
D12	GNDQ
D13	NC
D14	GBB2/IO42PPB1
D15	NC
D16	IO44NDB1
E1	IO113PDB3
E2	NC
E3	IO116VDB3
E4	IO115UDB3
E5	VMV0
E6	VCCIB0
E7	VCCIB0
E8	IO19RSB0

FG256	
Pin Number	A3P250 Function
E9	IO24RSB0
E10	VCCIB0
E11	VCCIB0
E12	VMV1
E13	GBC2/IO43PDB1
E14	IO46RSB1
E15	NC
E16	IO45PDB1
F1	IO113NDB3
F2	IO112PPB3
F3	NC
F4	IO115VDB3
F5	VCCIB3
F6	GND
F7	VCC
F8	VCC
F9	VCC
F10	VCC
F11	GND
F12	VCCIB1
F13	IO43NDB1
F14	NC
F15	IO47PPB1
F16	IO45NDB1
G1	IO111NDB3
G2	IO111PDB3
G3	IO112NPB3
G4	GFC1/IO110PPB3
G5	VCCIB3
G6	VCC
G7	GND
G8	GND
G9	GND
G10	GND
G11	VCC
G12	VCCIB1

FG256	
Pin Number	**A3P600 Function**
P9	IO107RSB2
P10	IO104RSB2
P11	IO97RSB2
P12	VMV1
P13	TCK
P14	VPUMP
P15	TRST
P16	GDA0/IO88NDB1
R1	GEA1/IO144PDB3
R2	GEA0/IO144NDB3
R3	IO139RSB2
R4	GEC2/IO141RSB2
R5	IO132RSB2
R6	IO127RSB2
R7	IO121RSB2
R8	IO114RSB2
R9	IO109RSB2
R10	IO105RSB2
R11	IO98RSB2
R12	IO96RSB2
R13	GDB2/IO90RSB2
R14	TDI
R15	GNDQ
R16	TDO
T1	GND
T2	IO137RSB2
T3	GEB2/IO142RSB2
T4	IO134RSB2
T5	IO125RSB2
T6	IO123RSB2
T7	IO118RSB2
T8	IO115RSB2
T9	IO111RSB2
T10	IO106RSB2
T11	IO102RSB2
T12	GDC2/IO91RSB2

FG256	
Pin Number	**A3P600 Function**
T13	IO93RSB2
T14	GDA2/IO89RSB2
T15	TMS
T16	GND

FG484	
Pin Number	A3P400 Function
A1	GND
A2	GND
A3	VCCIB0
A4	NC
A5	NC
A6	IO15RSB0
A7	IO18RSB0
A8	NC
A9	NC
A10	IO23RSB0
A11	IO29RSB0
A12	IO35RSB0
A13	IO36RSB0
A14	NC
A15	NC
A16	IO50RSB0
A17	IO51RSB0
A18	NC
A19	NC
A20	VCCIB0
A21	GND
A22	GND
B1	GND
B2	VCCIB3
B3	NC
B4	NC
B5	NC
B6	NC
B7	NC
B8	NC
B9	NC
B10	NC
B11	NC
B12	NC
B13	NC
B14	NC

FG484	
Pin Number	A3P400 Function
B15	NC
B16	NC
B17	NC
B18	NC
B19	NC
B20	NC
B21	VCCIB1
B22	GND
C1	VCCIB3
C2	NC
C3	NC
C4	NC
C5	GND
C6	NC
C7	NC
C8	VCC
C9	VCC
C10	NC
C11	NC
C12	NC
C13	NC
C14	VCC
C15	VCC
C16	NC
C17	NC
C18	GND
C19	NC
C20	NC
C21	NC
C22	VCCIB1
D1	NC
D2	NC
D3	NC
D4	GND
D5	GAA0/IO00RSB0
D6	GAA1/IO01RSB0

FG484	
Pin Number	A3P400 Function
D7	GAB0/IO02RSB0
D8	IO16RSB0
D9	IO17RSB0
D10	IO22RSB0
D11	IO28RSB0
D12	IO34RSB0
D13	IO37RSB0
D14	IO41RSB0
D15	IO43RSB0
D16	GBB1/IO57RSB0
D17	GBA0/IO58RSB0
D18	GBA1/IO59RSB0
D19	GND
D20	NC
D21	NC
D22	NC
E1	NC
E2	NC
E3	GND
E4	GAB2/IO154UDB3
E5	GAA2/IO155UDB3
E6	IO12RSB0
E7	GAB1/IO03RSB0
E8	IO13RSB0
E9	IO14RSB0
E10	IO21RSB0
E11	IO27RSB0
E12	IO32RSB0
E13	IO38RSB0
E14	IO42RSB0
E15	GBC1/IO55RSB0
E16	GBB0/IO56RSB0
E17	IO44RSB0
E18	GBA2/IO60PDB1
E19	IO60NDB1
E20	GND

Revision	Changes	Page
Revision 10 (continued)	"TBD" for 3.3 V LVCMOS Wide Range in Table 2-28 • I/O Output Buffer Maximum Resistances1 through Table 2-30 • I/O Output Buffer Maximum Resistances1 was replaced by "Same as regular 3.3 V" (SAR 33852).	2-26 to 2-28
	The equations in the notes for Table 2-31 • I/O Weak Pull-Up/Pull-Down Resistances were corrected (SAR 32470).	2-28
	"TBD" for 3.3 V LVCMOS Wide Range in Table 2-32 • I/O Short Currents IOSH/IOSL through Table 2-34 • I/O Short Currents IOSH/IOSL was replaced by "Same as regular 3.3 V LVCMOS" (SAR 33852).	2-29 to 2-31
	In the "3.3 V LVCMOS Wide Range" section, values were added to Table 2-47 through Table 2-49 for IOSL and IOSH, replacing "TBD" (SAR 33852).	2-39 to 2-40
	The following sentence was deleted from the "2.5 V LVCMOS" section (SAR 24916): "It uses a 5 V–tolerant input buffer and push-pull output buffer."	2-47
	The table notes were revised for Table 2-90 • LVDS Minimum and Maximum DC Input and Output Levels (SAR 33859).	2-66
	Values were added for $F_{DDRIMAX}$ and F_{DDOMAX} in Table 2-102 • Input DDR Propagation Delays and Table 2-104 • Output DDR Propagation Delays (SAR 23919).	2-78, 2-80
	Table 2-115 • ProASIC3 CCC/PLL Specification was updated. A note was added to indicate that when the CCC/PLL core is generated by Microsemi core generator software, not all delay values of the specified delay increments are available (SAR 25705).	2-90
	The following figures were deleted (SAR 29991). Reference was made to a new application note, *Simultaneous Read-Write Operations in Dual-Port SRAM for Flash-Based cSoCs and FPGAs*, which covers these cases in detail (SAR 21770). Figure 2-34 • Write Access after Write onto Same Address Figure 2-35 • Read Access after Write onto Same Address Figure 2-35 • Read Access after Write onto Same Address The port names in the SRAM "Timing Waveforms", SRAM "Timing Characteristics" tables, Figure 2-39 • FIFO Reset, and the FIFO "Timing Characteristics" tables were revised to ensure consistency with the software names (SARs 29991, 30510).	2-92, 2-94, 2-99 2-102
	The "Pin Descriptions" chapter has been added (SAR 21642).	3-1
	Package names used in the "Package Pin Assignments" section were revised to match standards given in *Package Mechanical Drawings* (SAR 27395).	4-1
July 2010	The versioning system for datasheets has been changed. Datasheets are assigned a revision number that increments each time the datasheet is revised. The "ProASIC3 Device Status" table on page IV indicates the status for each device in the device family.	N/A

Revision	Changes	Page
Advance v0.3	The "PLL Macro" section was updated. EXTFB information was removed from this section.	2-15
	The CCC Output Peak-to-Peak Period Jitter F_{CCC_OUT} was updated in Table 2-11 • ProASIC3 CCC/PLL Specification	2-29
	EXTFB was removed from Figure 2-27 • CCC/PLL Macro.	2-28
	Table 2-13 • ProASIC3 I/O Features was updated.	2-30
	The "Hot-Swap Support" section was updated.	2-33
	The "Cold-Sparing Support" section was updated.	2-34
	"Electrostatic Discharge (ESD) Protection" section was updated.	2-35
	The LVPECL specification in Table 2-43 • I/O Hot-Swap and 5 V Input Tolerance Capabilities in ProASIC3 Devices was updated.	2-64
	In the Bank 1 area of Figure 2-72, VMV2 was changed to VMV1 and VCCIB2 was changed to $VCC_I B1$.	2-97
	The VJTAG and I/O pin descriptions were updated in the "Pin Descriptions" section.	2-50
	The "JTAG Pins" section was updated.	2-51
	"128-Bit AES Decryption" section was updated to include M7 device information.	2-53
	Table 3-6 was updated.	3-6
	Table 3-7 was updated.	3-6
	In Table 3-11, PAC4 was updated.	3-93-8
	Table 3-20 was updated.	3-20
	The note in Table 3-32 was updated.	3-27
	All Timing Characteristics tables were updated from LVTTL to Register Delays	3-31 to 3-73
	The Timing Characteristics for RAM4K9, RAM512X18, and FIFO were updated.	3-85 to 3-90
	F_{TCKMAX} was updated in Table 3-110.	3-97
Advance v0.2	Figure 2-11 was updated.	2-9
	The "Clock Resources (VersaNets)" section was updated.	2-9
	The "VersaNet Global Networks and Spine Access" section was updated.	2-9
	The "PLL Macro" section was updated.	2-15
	Figure 2-27 was updated.	2-28
	Figure 2-20 was updated.	2-19
	Table 2-5 was updated.	2-25
	Table 2-6 was updated.	2-25
	The "FIFO Flag Usage Considerations" section was updated.	2-27
	Table 2-13 was updated.	2-30
	Figure 2-24 was updated.	2-31
	The "Cold-Sparing Support" section is new.	2-34